

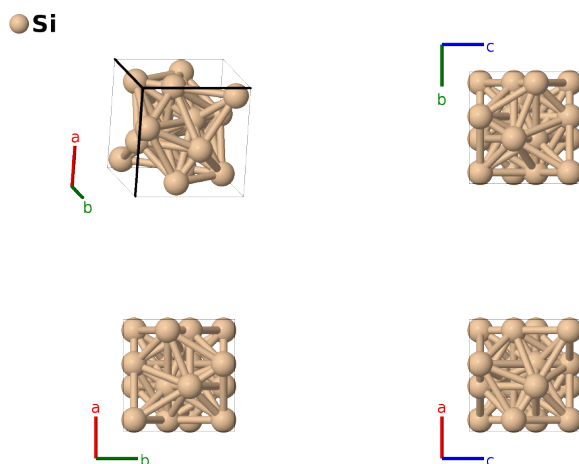
BC8 (Si) Structure: A_cI16_206_c-001

This structure originally had the label A_cI16_206_c. Calls to that address will be redirected here.

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<https://aflow.org/p/83MZ>

https://aflow.org/p/A_cI16_206_c-001



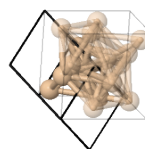
Prototype	Si
AFLOW prototype label	A_cI16_206_c-001
ICSD	none
Pearson symbol	cI16
Space group number	206
Space group symbol	$Ia\bar{3}$
AFLOW prototype command	<code>aflow --proto=A_cI16_206_c-001 --params=a, x₁</code>

- This is a tetragonally bonded structure which packs more efficiently than diamond. See (Crain, 1995) and references therein. The reference compound chosen here, found in (Wentorf, 1963), is stable in the range 11-16 GPa.

Body-centered Cubic primitive vectors

$$\begin{aligned} \mathbf{a}_1 &= -\frac{1}{2}a\hat{x} + \frac{1}{2}a\hat{y} + \frac{1}{2}a\hat{z} \\ \mathbf{a}_2 &= \frac{1}{2}a\hat{x} - \frac{1}{2}a\hat{y} + \frac{1}{2}a\hat{z} \\ \mathbf{a}_3 &= \frac{1}{2}a\hat{x} + \frac{1}{2}a\hat{y} - \frac{1}{2}a\hat{z} \end{aligned}$$

\mathbf{a}_3
 \mathbf{a}_2
 \mathbf{a}_1



Basis vectors

	Lattice coordinates	Cartesian coordinates	Wyckoff position	Atom type
\mathbf{B}_1	$= 2x_1 \mathbf{a}_1 + 2x_1 \mathbf{a}_2 + 2x_1 \mathbf{a}_3$	$= ax_1 \hat{\mathbf{x}} + ax_1 \hat{\mathbf{y}} + ax_1 \hat{\mathbf{z}}$	(16c)	Si I
\mathbf{B}_2	$= \frac{1}{2} \mathbf{a}_1 - (2x_1 - \frac{1}{2}) \mathbf{a}_3$	$= -ax_1 \hat{\mathbf{x}} - a(x_1 - \frac{1}{2}) \hat{\mathbf{y}} + ax_1 \hat{\mathbf{z}}$	(16c)	Si I
\mathbf{B}_3	$= -(2x_1 - \frac{1}{2}) \mathbf{a}_2 + \frac{1}{2} \mathbf{a}_3$	$= -a(x_1 - \frac{1}{2}) \hat{\mathbf{x}} + ax_1 \hat{\mathbf{y}} - ax_1 \hat{\mathbf{z}}$	(16c)	Si I
\mathbf{B}_4	$= -(2x_1 - \frac{1}{2}) \mathbf{a}_1 + \frac{1}{2} \mathbf{a}_2$	$= ax_1 \hat{\mathbf{x}} - ax_1 \hat{\mathbf{y}} - a(x_1 - \frac{1}{2}) \hat{\mathbf{z}}$	(16c)	Si I
\mathbf{B}_5	$= -2x_1 \mathbf{a}_1 - 2x_1 \mathbf{a}_2 - 2x_1 \mathbf{a}_3$	$= -ax_1 \hat{\mathbf{x}} - ax_1 \hat{\mathbf{y}} - ax_1 \hat{\mathbf{z}}$	(16c)	Si I
\mathbf{B}_6	$= \frac{1}{2} \mathbf{a}_1 + (2x_1 + \frac{1}{2}) \mathbf{a}_3$	$= ax_1 \hat{\mathbf{x}} + a(x_1 + \frac{1}{2}) \hat{\mathbf{y}} - ax_1 \hat{\mathbf{z}}$	(16c)	Si I
\mathbf{B}_7	$= (2x_1 + \frac{1}{2}) \mathbf{a}_2 + \frac{1}{2} \mathbf{a}_3$	$= a(x_1 + \frac{1}{2}) \hat{\mathbf{x}} - ax_1 \hat{\mathbf{y}} + ax_1 \hat{\mathbf{z}}$	(16c)	Si I
\mathbf{B}_8	$= (2x_1 + \frac{1}{2}) \mathbf{a}_1 + \frac{1}{2} \mathbf{a}_2$	$= -ax_1 \hat{\mathbf{x}} + ax_1 \hat{\mathbf{y}} + a(x_1 + \frac{1}{2}) \hat{\mathbf{z}}$	(16c)	Si I

References

- [1] J. R. H. Wentorf and J. S. Kasper, *Two New Forms of Silicon*, *Science* **139**, 338–339 (1963), doi:10.1126/science.139.3552.338.b.
- [2] J. Crain, S. J. Clark, G. J. Ackland, M. C. Payne, V. Milman, P. D. Hatton, and B. J. Reid, *Theoretical study of high-density phases of covalent semiconductors. I. Ab initio treatment*, *Phys. Rev. B* **49**, 5329–5340 (1994), doi:10.1103/PhysRevB.49.5329.